

## PUBLICATIONS IN REFEREED JOURNALS

1. "Current conduction mechanism and electrical break-down in InN grown on GaN", J. Kuzmík, C. Fleury, A. Adikimenakis, D. Gregušová, M. Čapajna, E. Dobročka, Š. Haščík, M. Kučera, R. Kúdela, M. Androulidaki, D. Pogany, and A. Georgakilas, **Appl. Phys. Lett.** **110**, 232103 (2017)
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2. “*AlN/GaN/AlN double heterostructures with thin AlN top barriers*”, Ch. Zervos, A. Bairamis, A. Adikimenakis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis & A. Georgakilas, **ASDAM 2014 Conference Proceedings**, pp. 113-116 (IEEE, 2014). *IEEE Catalog Number: CFP14469-PRT, ISBN: 978-1-4799-5474-2*.
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